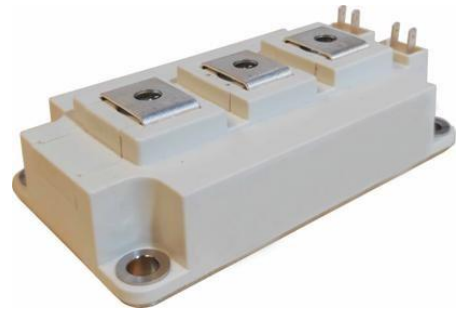# QMFF150R12EF
1200V 150A IGBT Module

Electrical Features

- Trench/Fieldstop IGBT
- Half-bridge
- Standard package
- Including anti-parallel FWD

Typical Applications

- UPS System
- Motor Drivers
- Welding Machine
- High Frequency Swithing Application

IGBT，Inverter

Maximum Rated Values					
Symbol	Item	Conditions		Rating	Unit
IGBT					
V_{CES}	Collector-emitter voltage	T_{vj}=25°C		1200	V
V_{GES}	Gate-emitter voltage	-		±20	V
I_C	Collector current,DC	T_C=100°C,T_{vj}=175°C		150	A
I_{CRM}	Repetitive peak collector current	t_p=1ms		300	A
P_{tot}	Total power dissipation	T_C=25°C,T_{vj}=175°C		937	W

Characteristics Values							
Symbol	Item	Conditions		Min.	Typ.	Max.	Unit
IGBT							
I_{CES}	Collector-emitter cut-off current	V_{CE}=1200V,V_{GE}=0V,T_{vj}=25°C		-	-	1	mA
I_{GES}	Gate leakage current	V_{CE}=0V,V_{GE}=20V,T_{vj}=25°C		-	-	250	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=5.7mA,V_{CE}=V_{GE},T_{vj}=25°C		5	5.8	7	V
V_{CEsat}	Collector-emitter saturation voltage	I_C=150A V_{GE}=15V	T_{vj}=25°C	-	1.81	2.3	V
			T_{vj}=125°C	-	2.16	-	
			T_{vj}=150°C	-	2.26	-	
C_{ies}	Input capacitance	V_{CE}=25V,V_{GE}=0V		-	9.7	-	nF
C_{res}	Reverse transfer capacitance	f=1MHz,T_{vj}=25°C		-	0.3	-	
Q_G	Gate charge	V_{CC}=600V, I_C=150A, V_{GE}=15V		-	1.2	-	μC

Symbol	Item	Conditions						Unit
$t_{d(on)}$	Turn-on delay time			T_{vj}=25°C	-	81.6	-	ns
				T_{vj}=125°C	-	93.2	-	
				T_{vj}=150°C	-	95.4	-	
t_r	Rise time	V_{CC}=600V		T_{vj}=25°C	-	38.5	-	
		I_C=150A		T_{vj}=125°C	-	42.1	-	
		V_{GE}=±15V		T_{vj}=150°C	-	43.2	-	
$t_{d(off)}$	Turn-off delay time	$R_{G(on)}$=10 Ω		T_{vj}=25°C	-	243.2	-	
		$R_{G(off)}$=10 Ω		T_{vj}=125°C	-	265.6	-	
		Inductive load		T_{vj}=150°C	-	272.0	-	
t_f	Fall time			T_{vj}=25°C	-	164.8	-	
				T_{vj}=125°C	-	192.0	-	
				T_{vj}=150°C	-	211.2	-	
E_{on}	Turn-on energy (per pulse)	V_{CC}=600V，I_C=150A V_{GE}=±15V，$R_{G(on)}$=10Ω di/dt=8780A/μs(T_{vj}=150°C)		T_{vj}=25°C	-	9.40	-	mJ
				T_{vj}=125°C	-	13.16	-	
				T_{vj}=150°C	-	14.71	-	
E_{off}	Turn-off energy (per pulse)	V_{CC}=600V，I_C=150A V_{GE}=±15V，$R_{G(off)}$=10Ω du/dt=6800V/μs(T_{vj}=150°C)		T_{vj}=25°C	-	7.39	-	
				T_{vj}=125°C	-	9.81	-	
				T_{vj}=150°C	-	10.31	-	
R_{thJC}	Thermal resistance,junction to case	per IGBT			-	-	0.16	K/W
R_{thCH}	Thermalresistance,case to heatsink	per IGBT/ λgrease=1W/(m·K)			-	0.03	-	K/W
T_{vjop}	Temperature under switching conditions				-40		150	°C

Diode，Inverter
Maximum Rated Values

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	T_{vj}=25°C	1200	V
I_F	Forward current,DC		60	A
I_{FRM}	Repetitive peak forward current	t_p=1ms	120	A

Characteristic Values

Symbol	Item	Conditions						Unit
V_F	Continuous forward voltage	I_F=60A V_{GE}=0V		T_{vj}=25°C	-	1.86	2.3	V
				T_{vj}=125°C	-	1.57	-	
				T_{vj}=150°C	-	1.48	-	
I_{RM}	Peak reverse recovery current			T_{vj}=25°C	-	164	-	A
				T_{vj}=125°C	-	180	-	
				T_{vj}=150°C	-	192	-	
t_{rr}	Reverse recovery time	V_R=600V I_F=150A V_{GE}=-15V -di$_F$/dt=5200A/μs (T_{vj}=150°C)		T_{vj}=25°C	-	68.7	-	ns
				T_{vj}=125°C	-	114.9	-	
				T_{vj}=150°C	-	138.6	-	
Q_r	Recovered charge			T_{vj}=25°C	-	6.0	-	μC
				T_{vj}=125°C	-	20.6	-	
				T_{vj}=150°C	-	24.7	-	
E_{rec}	Reverse recovery energy			T_{vj}=25°C	-	2.69	-	mJ
				T_{vj}=125°C	-	11.86	-	
				T_{vj}=150°C	-	14.16	-	

R_{thJC}	Thermal resistance, junction to case	per diode	-	-	0.3	K/W
R_{thCH}	Thermal resistance,case to heatsink	per diode/ λgrease=1W/(m·K)	-	0.06	-	K/W
T_{vjop}	Temperature under switching conditions		-40		150	°C

Module

Symbol	Item	Conditions	Rating			Unit
V_{ISOL}	Isolation voltage	Terminals to baseplate，RMS,f=50Hz,t=1min	2500			V
-	Material of module baseplate	-	Cu			-
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al_2O_3			-
T_{stg}	Storage temperature	-	-40~125			°C

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
M	Mounting torque for module mounting	Screw M6	3.0	-	6.0	Nm
	Terminal connection torque	Screw M6	2.5	-	5.0	Nm
ds	Creepage distance	Terminal to terminal	-	23	-	mm
		Terminal to base plate	-	29	-	
da	Clearance	Terminal to terminal	-	11	-	mm
		Terminal to base plate	-	23	-	
m	Weight	-	-	315	-	g

output characteristic IGBT, Inverter (typical)
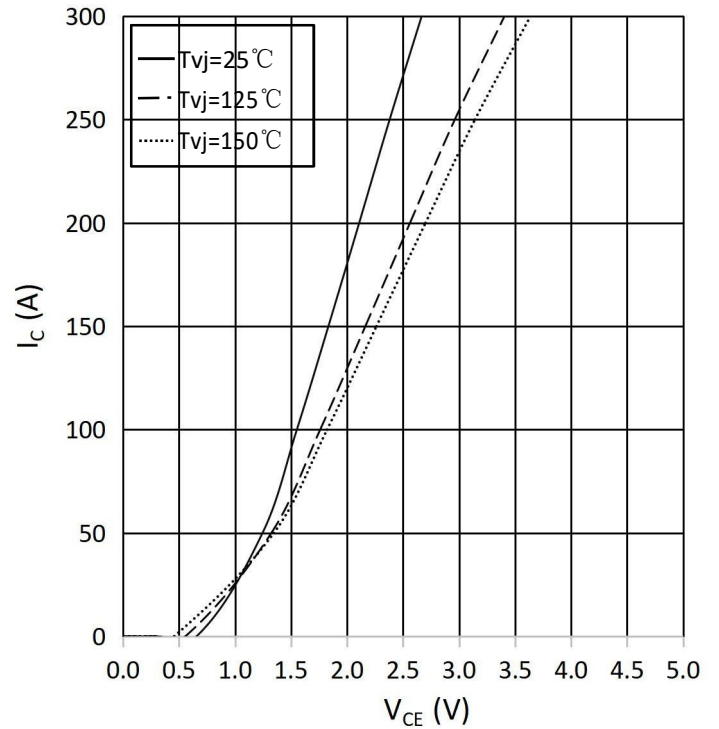
$I_C = f(V_{CE})$

$T_{vj} = 150℃$
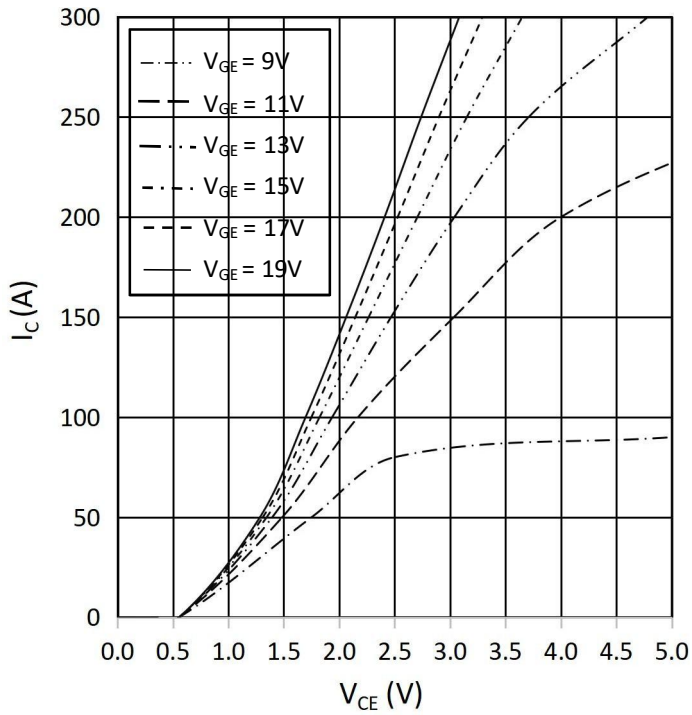
output characteristic IGBT, Inverter (typical)
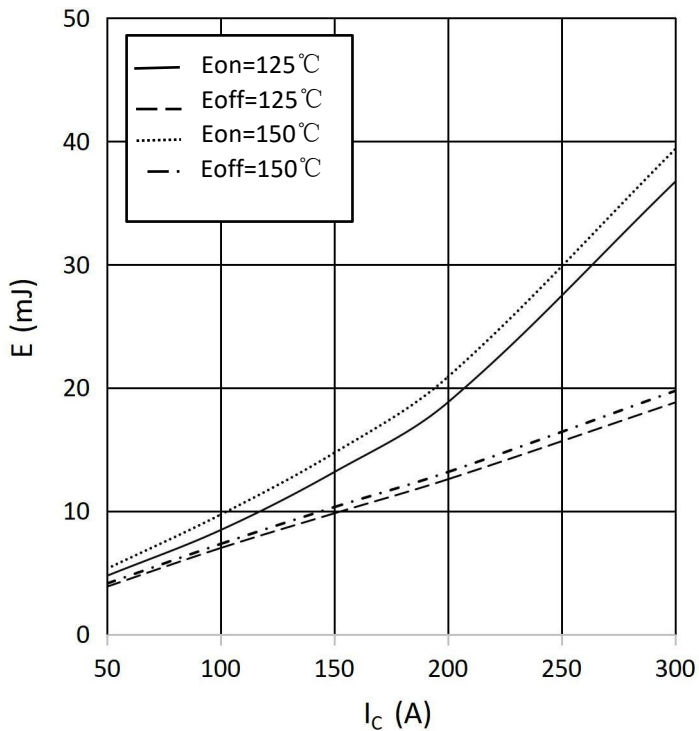
$I_C = f(V_{CE})$

$V_{GE} = 15\ V$

switching losses IGBT,Inverter(typical)

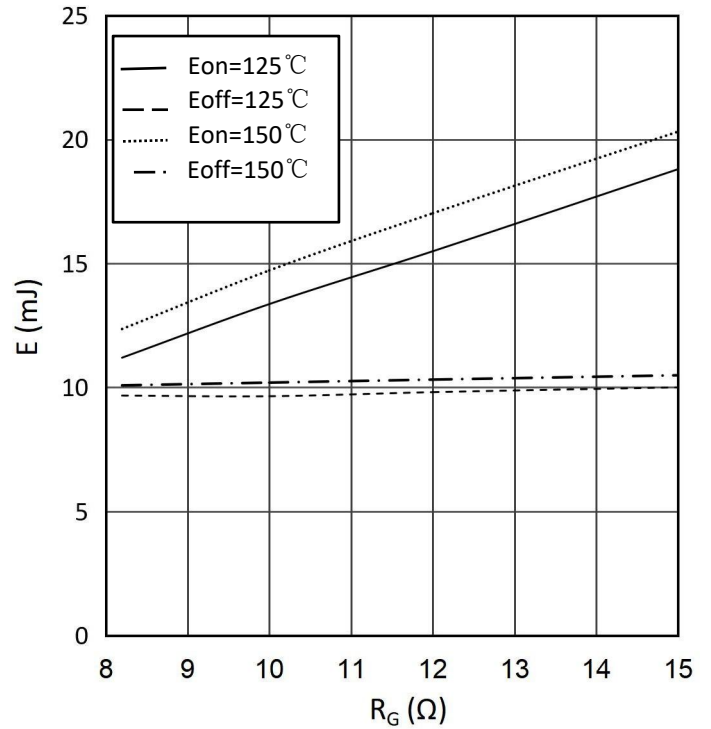$E_{on} = f(I_C),\ E_{off} = f(I_C)$

$V_{GE} = ±15V,\ R_{Gon} = 10Ω,\ R_{Goff} = 10Ω,\ V_{CE} = 600V$

switching losses IGBT,Inverter(typical)

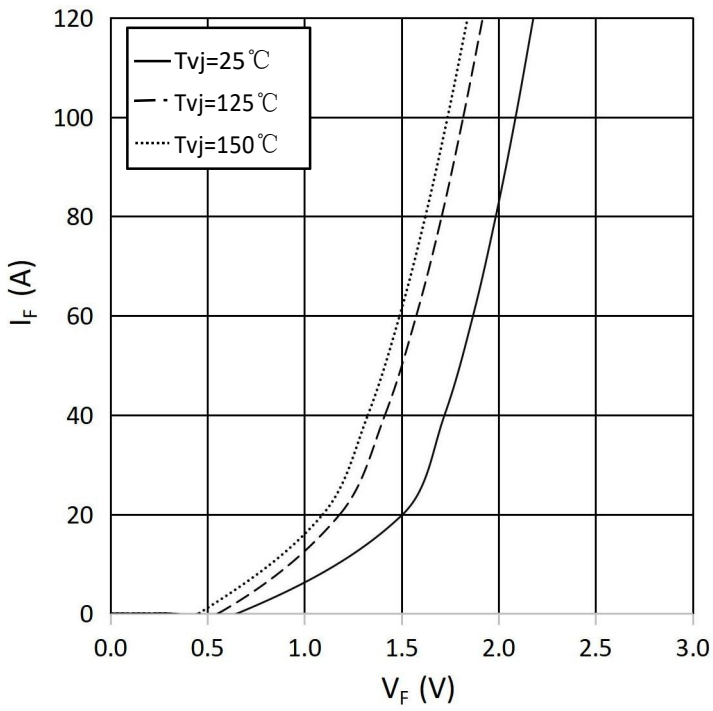$E_{on} = f(R_G),\ E_{off} = f(R_G)$

$V_{GE} = ±15V,\ I_C = 150A,\ V_{CE} = 600V$
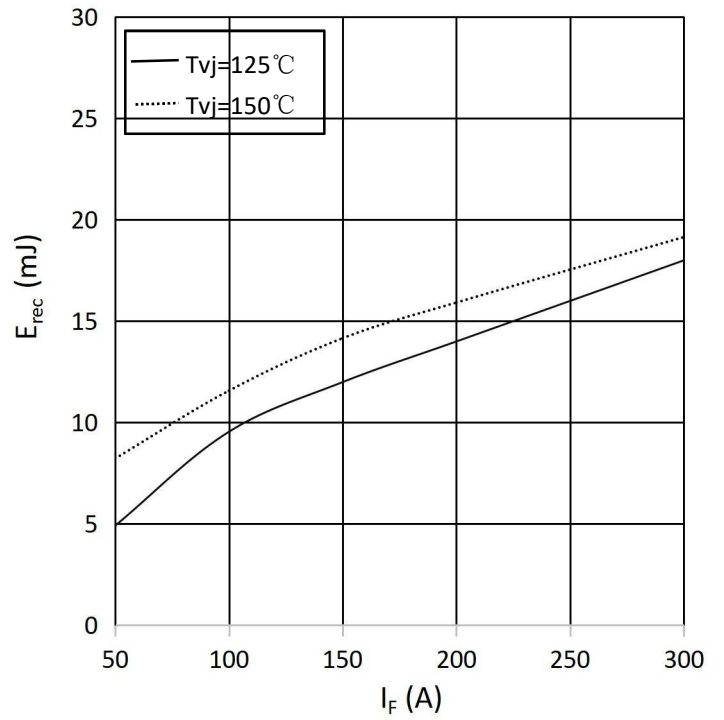

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forward characteristic of Diode, Inverter (typical)
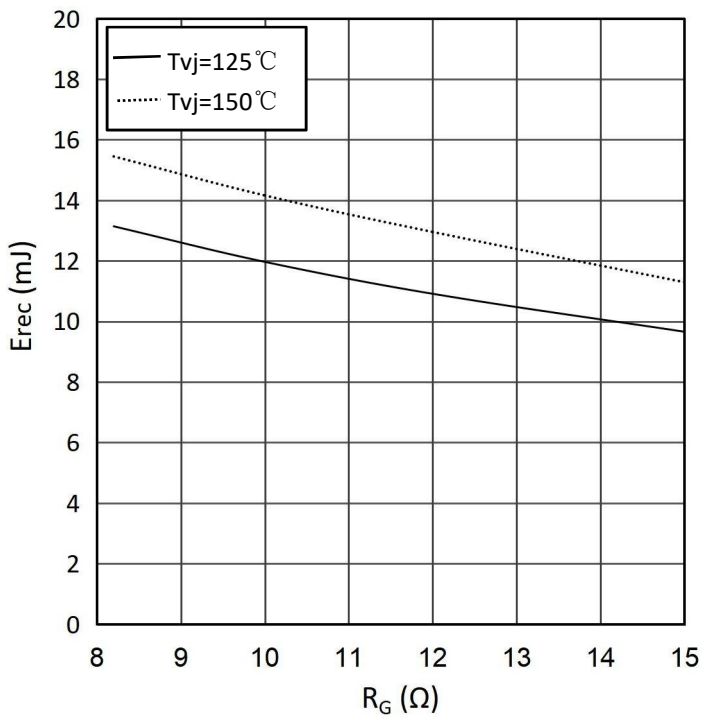
$I_F = f(V_F)$

switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
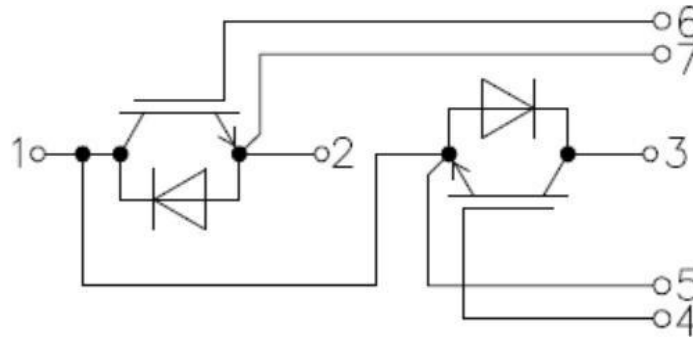
$R_{Gon} = 10\Omega$, $V_{CE} = 600V$

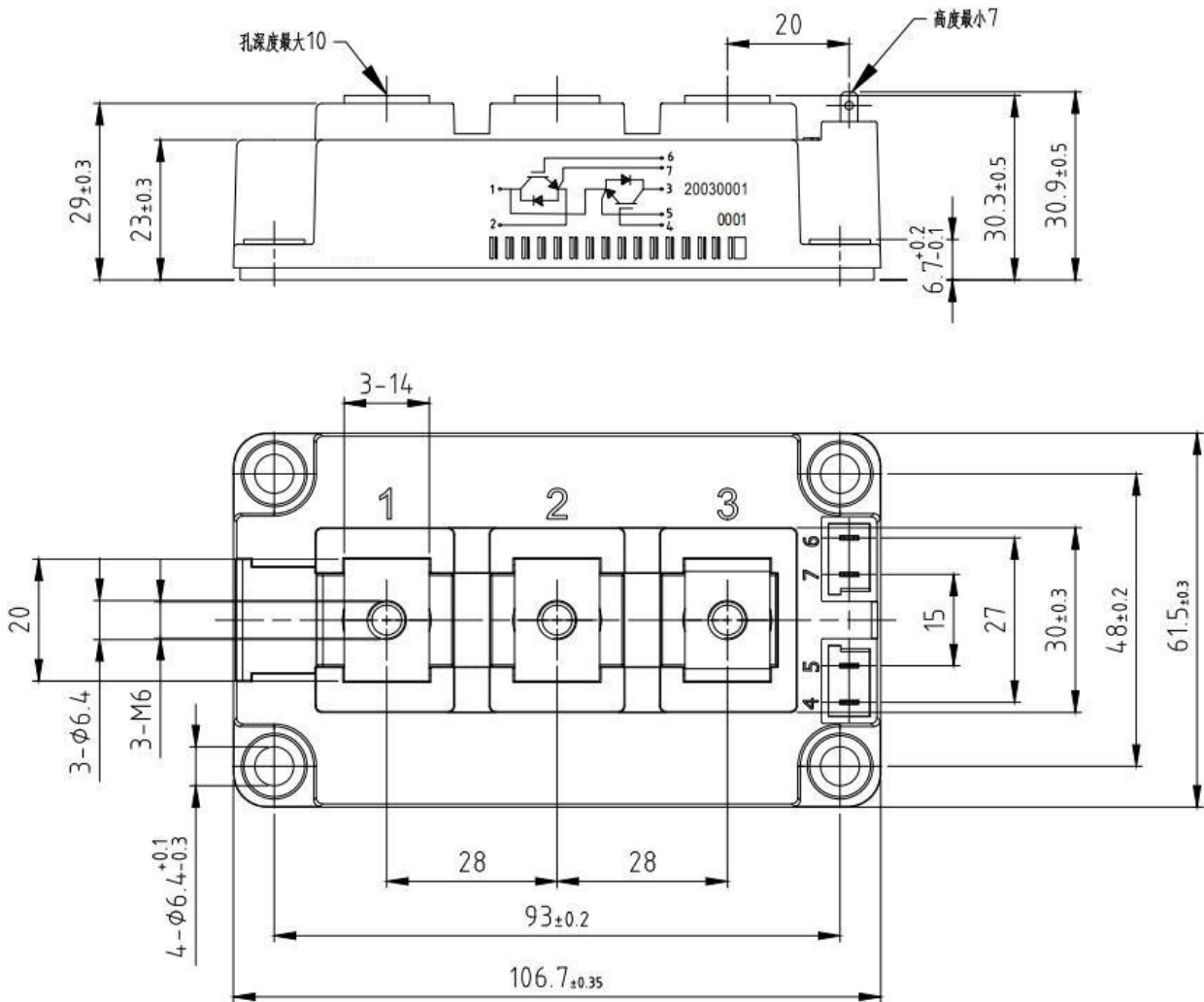**switching losses Diode, Inverter (typical)**

$E_{rec} = f(R_G)$

$I_F = 150A$, $V_{CE} = 600V$

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Circuit diagram headline

Package outlines（Unit：mm）

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